

KSC1187

TV 1st, 2nd Picture IF Amplifier (Forward AGC)

High Current Gain Bandwidth Product : f_T=700MHz
 High Power Gain : G_{PE}=24dB (TYP.) at f=45MHz



1. Emitter 2. Base 3. Collector

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{CBO}	Collector-Base Voltage	30	V
V _{CEO}	Collector-Emitter Voltage	20	V
V _{EBO}	Emitter-Base Voltage	4	V
I _C	Collector Current	30	mA
P _C	Collector Power Dissipation	250	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C}=10\mu A, I_{E}=0$	30			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C=5mA$, $I_B=0$	25			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_{E}=10\mu A, I_{C}=0$	4			V
I _{CBO}	Collector Cut-off Current	V _{CB} =20V, I _E =0			0.1	μΑ
h _{FE}	DC Current Gain	V _{CE} =10V, I _C =2mA	40		240	
f _T	Current Gain Bandwidth Product	V _{CE} =10V, I _C =3mA	400	700		MHz
C _{RE}	Reverse Transfer Capacitance	V _{CB} =10V, I _E =0, f=1MHz		0.6		pF
G _{PE}	Power Gain	V _{CE} =10V, I _C =3mA f=45MHz	20	24		dB
V _{AGC}	AGC Voltage	G _R = 30dB, f=45MHz	4.4	5.2	6.0	V

h_{FE} Classification

Classification	R	0	Y
h _{FE}	40 ~ 80	70 ~ 140	120 ~ 240

Typical Characteristics

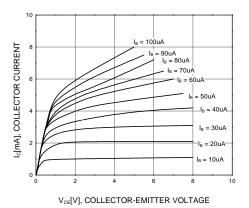


Figure 1. Static Characteristic

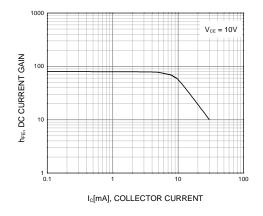


Figure 2. DC current Gain

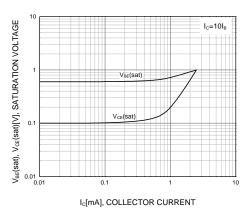


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

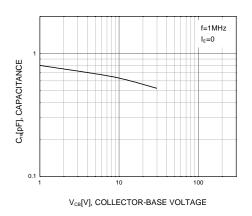


Figure 4. Reverse Capacitance

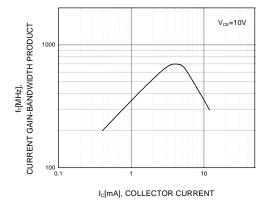
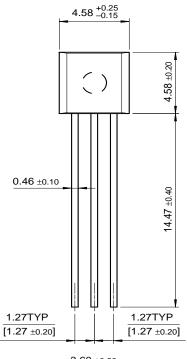


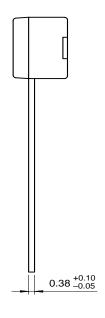
Figure 5. Current Gain Bandwidth Product

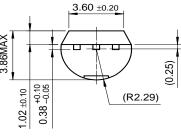
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Package Demensions

TO-92







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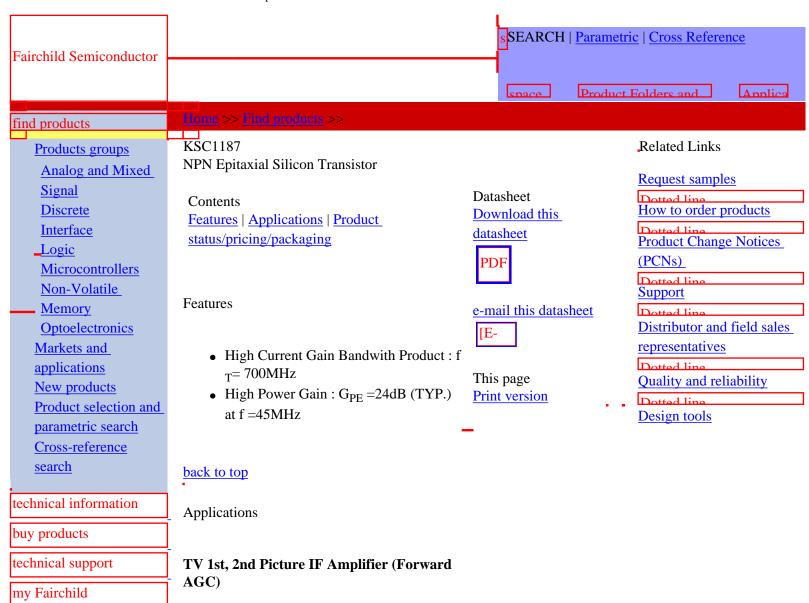
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Datasheet Identification	Product Status	Definition
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Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSC1187OBU	Full Production	\$0.05	<u>TO-92</u>	3	BULK
KSC1187YTA	Full Production	\$0.05	<u>TO-92</u>	3	TAPE REEL
KSC1187OTA	Full Production	\$0.05	<u>TO-92</u>	3	TAPE REEL
KSC1187YBU	Full Production	\$0.05	<u>TO-92</u>	3	BULK

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